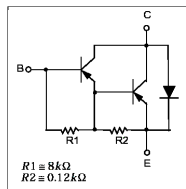


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TO-220F PNP Silicon PNP transistor in a TO-220F Plastic Package.

TIP122F
Complement to TIP122F.

Medium power linear switching applications.

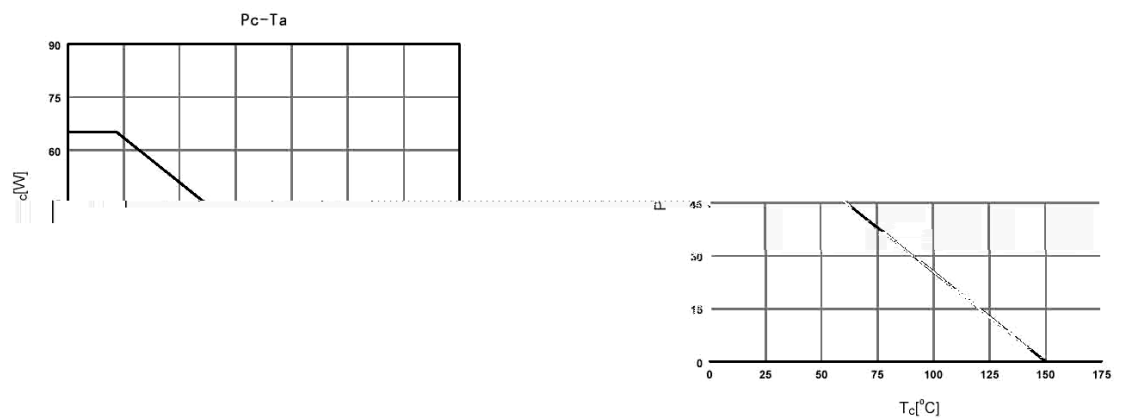
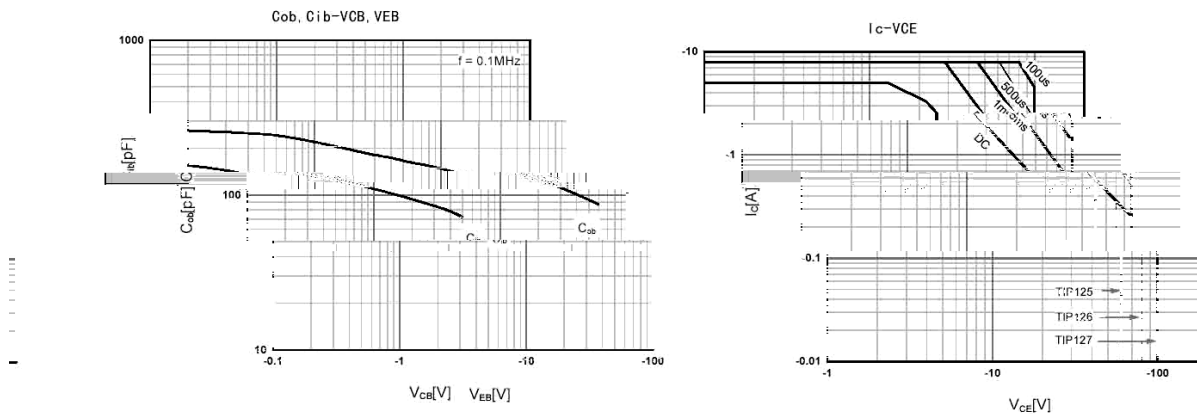
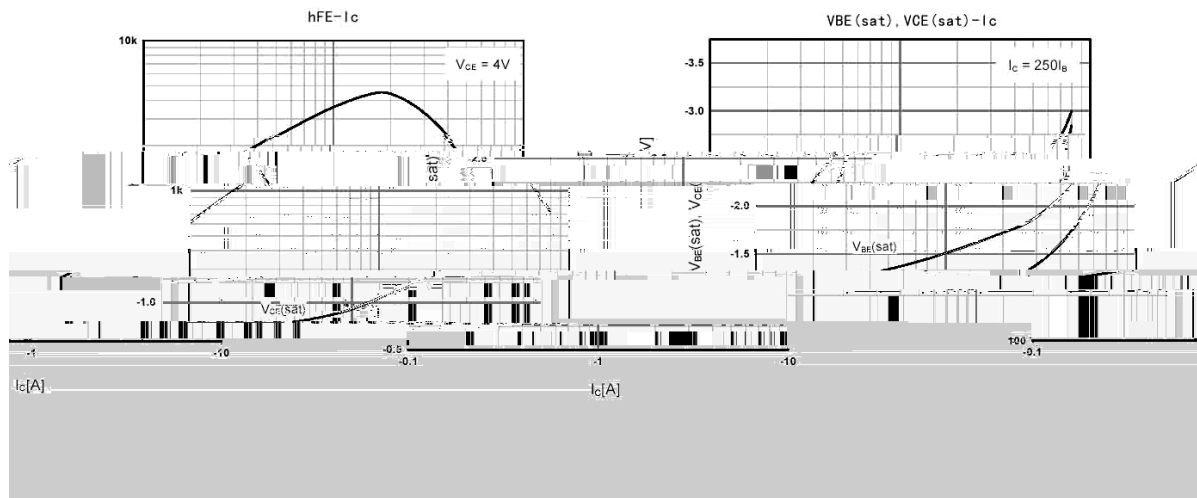


PIN1 Base PIN 2 Collector PIN 3 Emitter

See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-100	V
Collector to Emitter Voltage	V_{CEO}	-100	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-5.0	A
Collector Current – Continuous(Pulse)	I_{CP}	-8.0	A
Base Current	I_B	-120	mA
Collector Power Dissipation	P_C	2.0	W
	$P_C(T_c=25^\circ\text{C})$	60	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

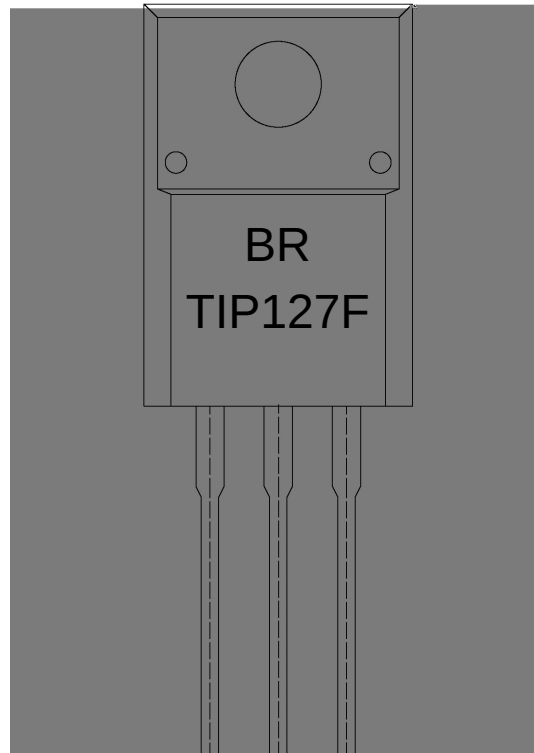
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-100\text{mA}$ $I_B=0$	-100			V
Collector Cut-Off Current	I_{CEO}	$V_{CE}=-50\text{V}$ $I_B=0$			-2.0	mA
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-100\text{V}$ $I_E=0$			-1.0	mA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-5.0\text{V}$ $I_C=0$			-2.0	mA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-3.0\text{V}$ $I_C=-0.5\text{A}$	1000			
	$h_{FE(2)}$	$V_{CE}=-3.0\text{V}$ $I_C=-3.0\text{A}$	1000			
Collector to Emitter Saturation Voltage	$V_{CE(sat)(1)}$	$I_C=-3.0\text{A}$ $I_B=-12\text{mA}$			-2.0	V
	$V_{CE(sat)(2)}$	$I_C=-5.0\text{A}$ $I_B=-20\text{mA}$	I		-4.0	V





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BR

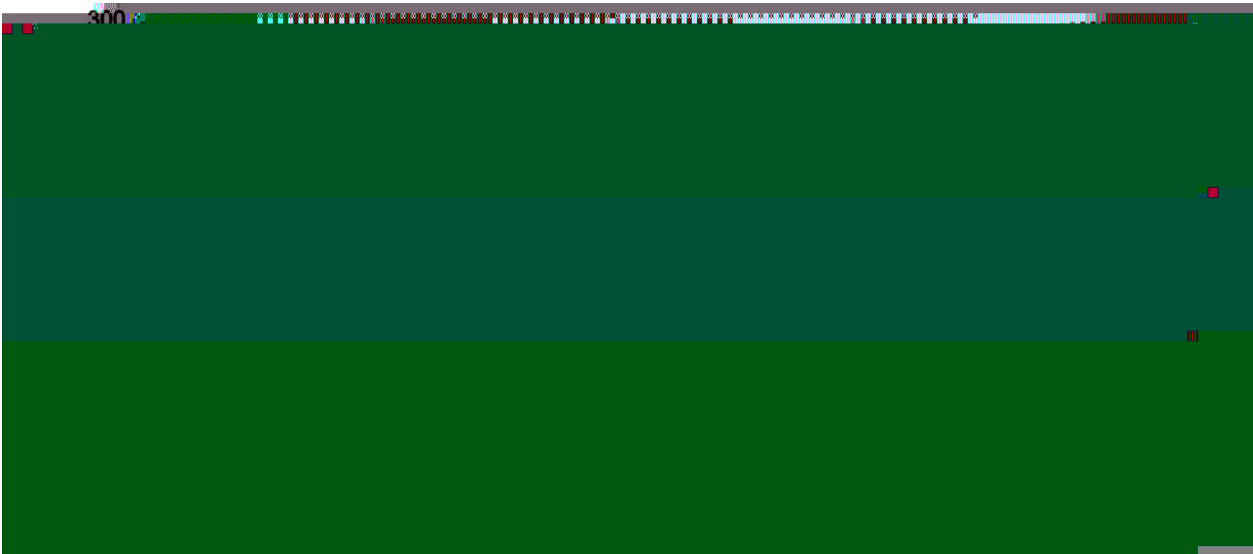
TIP127F

Note:

BR: Company Code.

TIP127F: Product Type Code.

****: Lot No. Code, code change with Lot No.



- 1

25 150

60 90sec;

1.Preheating:25~150 , Time:60~90sec.
- 2

255±5

5±0.5sec;

2.Peak Temp.:255±5 , Duration:5±0.5sec.
- 3

2 10

/sec.

3. Cooling Speed: 2~10 /sec.

270±5

10±1 sec.

Temp:270±5

Time:10±1 sec

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)		
	只袋	袋盒	只盒	盒箱	只箱	袋	盒	箱

/ TUBE

Package Type 封装形式	Units 包装数量	Dimension 包装尺寸 (unit: mm3)